DT09 R PCT/PTO 1 2 JAN 2005

FORM PTO-1449	SERIAL NO.	CASE NO.
	Not Assigned	10808/201
LIST OF PATENTS AND PUBLICATIONS FOR	FILING DATE	GROUP ART UNIT
APPLICANT'S INFORMATION DISCLOSURE	January 12, 2004	321 Nat 98 ned
STATEMENT		
(use several sheets if necessary)	APPLICANT(S): Georg Tempel	

REFERENCE DESIGNATION	U.S. PATENT DOCUMENTS

EXAMINER		DOCUMENT			CLASS/ SUBCLASS	FILING
INITIAL		NUMBER Number-Kind Code (if Known)	DATE	NAME	SUBCLASS	DATE
	A1	5,810,924	9/22/1998	Legoues et al.		6/7/1995
	A2	5,569,538	10/29/1996	Cho		10/14/1994
	A3	5,232,862	8/3/1993	Heremans et al.		1/13/1992
	A4					
	A5					
	A6					
	A7					
	A8					
	A9					
	A10					
	A11					
	A12					
	A13					

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (if known)	DATE	COUNTRY	SUBCLASS	TRANSLATION YES OR NO
	A14	EP 1 120 818 A1	8/1/2001	EPO		No
	A15	11233440	8/27/1999	EPO		Yes
	A16					
	A17					
	A18					

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.		
	A19	Tsutomu Tezuka, Naoharu Sugiyama, Tomohisa Mizuno and Shin-ichi Takagi "High Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique" 2002 Symposium on VLSI Technology Digest of Technical Papers, pp. 96-97	
	A20	T. Tezuka; N. Sugiyama, S. Takagi "Fabrication of a Strained is on sub-10-nm-thick SiGe-on-insulator virtual substrate" Materials and Science Engineering B89, 2002, pp. 360-363	
	A21	D.L. Harame, J.H. Comfort, J.D. Cressler, E.F. Crabbé, J.YC Sun, B.S. Meyerson, T. Tice "Sil/SiGe Epitaxial-Base Transistors-Part II: Process integration and Analog Applications" IEEE Transactions on Electron Devices, Volume 42, No. 3, March 1995, pp. 469-482	

EXAMINER	/Howard Weiss/	DATE CONSIDERED	01/28/2008			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;						

Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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DT09 Rec'd FC 12 JAN 2005

FORM PTO-1449

SERIAL NO.

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(use several sheets if necessary)

APPLICANT(S): Georg Tempel

EXAMINER INITIAL	(Ir syn	OTHER ART – NON PATENT LITERATURE DOCUMENTS include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, iposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
	A22	H. Zogg "Strain Relief in Epitaxial Flouride Buffer Layers for Semiconductor Heteroepitaxy" Applied Physics Letters, No. 15, October 13, 1986, pp. 933-935
	A23	
	A24	

EXAMINER	/Howard Weiss/	DATE CONSIDERED	01/28/2008	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.